Product catalog

LDMOS Power Amplifiers

LDMOS power amplifiers use laterally diffused MOS transistors to increase RF output power. Matching, bias, signal peaks and the complete thermal path determine their operating limits.



Products: 2

Revision: 2 · Revision date: 2026-11-11



LCPAM-20-520-200A

20–520 MHz 200 W Saturated LDMOS RF Power Amplifier Module

This LDMOS final-stage module covers 20–520 MHz with 200 W typical saturated output. Its 1 dB compression output is separately specified at 50 W typical, with 53 dB typical small-signal gain.

Operating frequency: Symbol: BW; Minimum: 20; Maximum: 520; Unit: MHz

Saturated RF output power: Symbol: Psat; Typical: 200; Unit: W

Output power at 1 dB compression: Symbol: P1dB; Typical: 50; Unit: W

Small-signal gain: Symbol: G; Typical: 53; Unit: dB

25 °C; 50 Ω

Product details Product datasheet



LCPAM-20-520-350

20–520 MHz LDMOS RF Power Amplifier, 350 W Typical Saturated Output

The LDMOS amplifier covers 20–520 MHz with 350 W typical saturated output and 150 W typical output at 1 dB compression. Typical gain is 56 dB, with 29 A typical current at 350 W and 48 VDC typical supply.

Operating frequency: Symbol: BW; Minimum: 20; Maximum: 520; Unit: MHz

Output power at 1 dB compression: Symbol: P-1dB; Typical: 150; Unit: W

RF output power @ PSAT: Symbol: PSAT; Typical: 350; Unit: W

Power gain @ PSAT: Symbol: Gp; Typical: 56; Unit: dB

+48.0VDC; 25°C; 50Ω

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Document notice

Specifications are subject to revision. Before design release, confirm the current document revision and product-specific requirements with LCRF. The approved quotation and order documentation define the supplied configuration.